
EE434
ASIC & Digital Systems

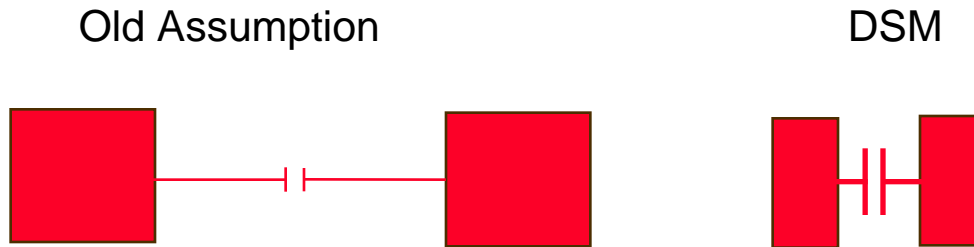
Partha Pande
School of EECS
Washington State University
pande@eecs.wsu.edu

Lecture 11

Physical Design Issues

Interconnect Scaling Effects

- Dense multilayer metal increases coupling capacitance



- Long/narrow line widths further increases resistance of interconnect



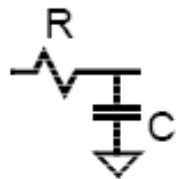
Wire Modeling

Wires are a distributed RC circuit

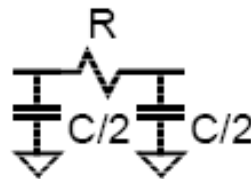
- Wire has r = resistance/mm and c = capacitance/mm

How should you model the interconnect for hand calc?

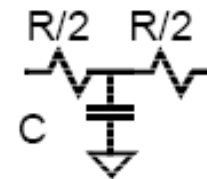
Use a simple L, Π , or T model assuming $C = cL$ and $R = rL$



L



Π



T

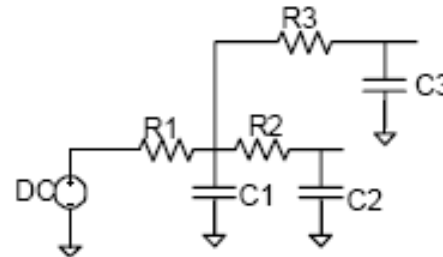
- One of the three models above is not useful for distributed RC modeling
 - Even with proper modeling, we still have to deal with RC trees
-

Elmore Delay

- ❑ Follow board notes
-

Elmore Delay

$$\tau_i = \sum R_{ik} \sum C_k$$



- C_k = every capacitance in the network in sequence
- R_{ik} = common resistance in path between source and node i and source and node k

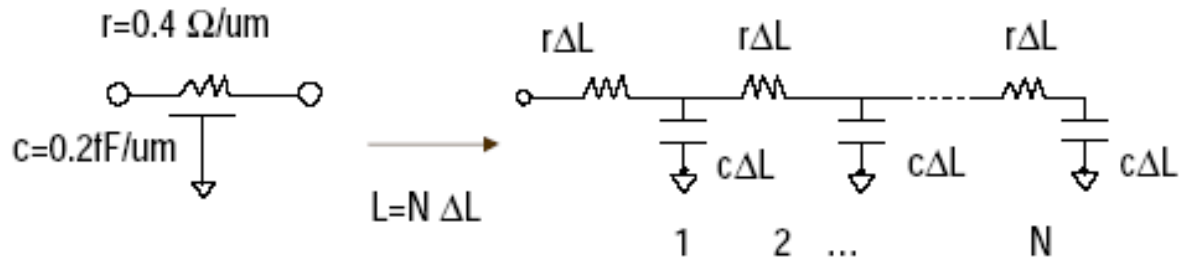
$$\tau_1 = R1C1 + R1C2 + R1C3$$

$$\tau_2 = R1C1 + (R1+R2)C2 + R1C3$$

$$\tau_3 = R1C1 + R1C2 + (R1+R3)C3$$

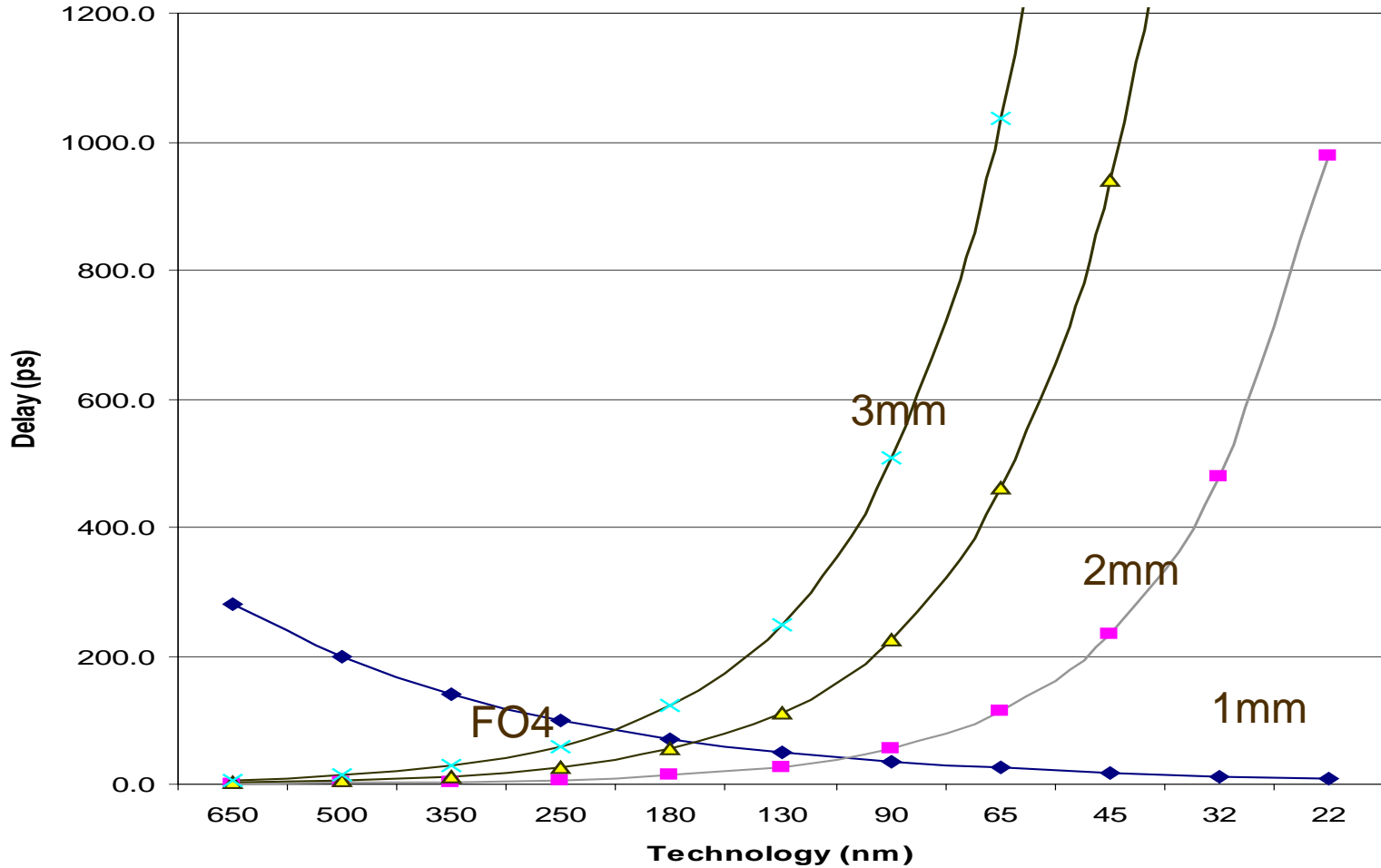
Delay of a wire

- What is the delay along the distributed line as a function on length L ?



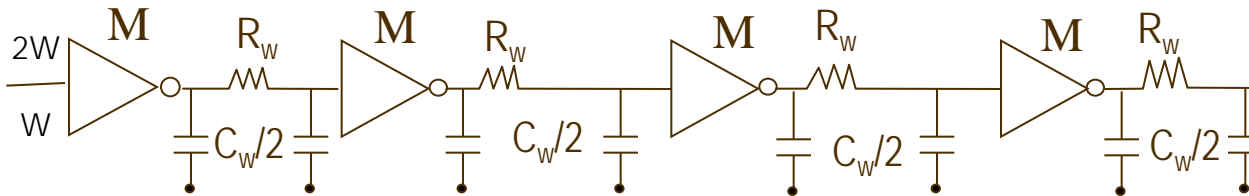
$$\begin{aligned} \text{Use Elmore delay} &= (r \Delta L)(c \Delta L) + 2(r \Delta L)(c \Delta L) + \dots + N(r \Delta L)(c \Delta L) \\ &= (\Delta L)^2 rc(1 + 2 + \dots + N) \\ &= (\Delta L)^2 rc(N)(N+1)/2 \approx (\Delta L)^2 rcN^2 \\ &= L^2 rc/2 = RC/2 \text{ (according to Elmore)} \\ &\approx 0.4rcL^2 \text{ (measured)} \quad \text{Note that delay is proportional to length}^2 \end{aligned}$$

FO4 vs. Wire Delay



Buffer Insertion for Long Wires

- Make Long wires into short wires by inserting buffers periodically. Divide interconnect into N sections as follows:



$$R_{\text{eff}} = R_{\text{eqn}}/M \quad C_{\text{self}} = C_j 3W * M \quad C_{\text{fanout}} = C_g 3W * M \quad R_w = R_{\text{int}} L/N \quad C_w = C_{\text{int}} L/N$$

- Then delay through buffers and interconnect is given by:

$$t_p = N * [R_{\text{eff}} (C_{\text{self}} + C_w/2) + (R_{\text{eff}} + R_w) (C_w/2 + C_{\text{fanout}})]$$

- What is the optimal number of buffers?

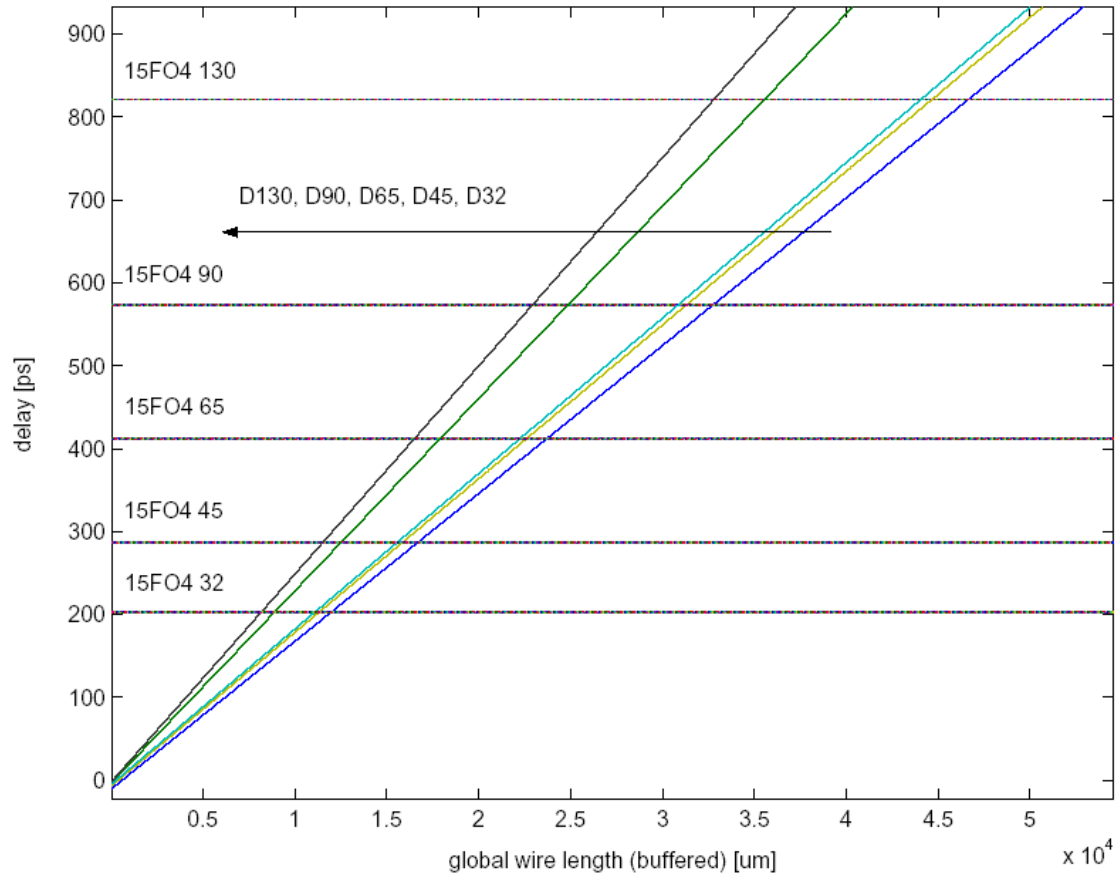
$$\text{Find } N \text{ such that } \partial t_p / \partial N = 0 \Rightarrow N \approx \text{sqrt}(0.4 R_{\text{int}} C_{\text{int}} L^2 / t_{\text{pbuf}})$$

$$\text{where } t_{\text{pbuf}} = R_{\text{eff}} (C_{\text{self}} + C_{\text{fanout}})$$

- What size should the buffers be?

$$\text{Find } M \text{ such that } \partial t_p / \partial M = 0 \Rightarrow M = \text{sqrt}((R_{\text{eqn}}/C_g 3W) (C_{\text{int}}/R_{\text{int}}))$$

Global wire delay

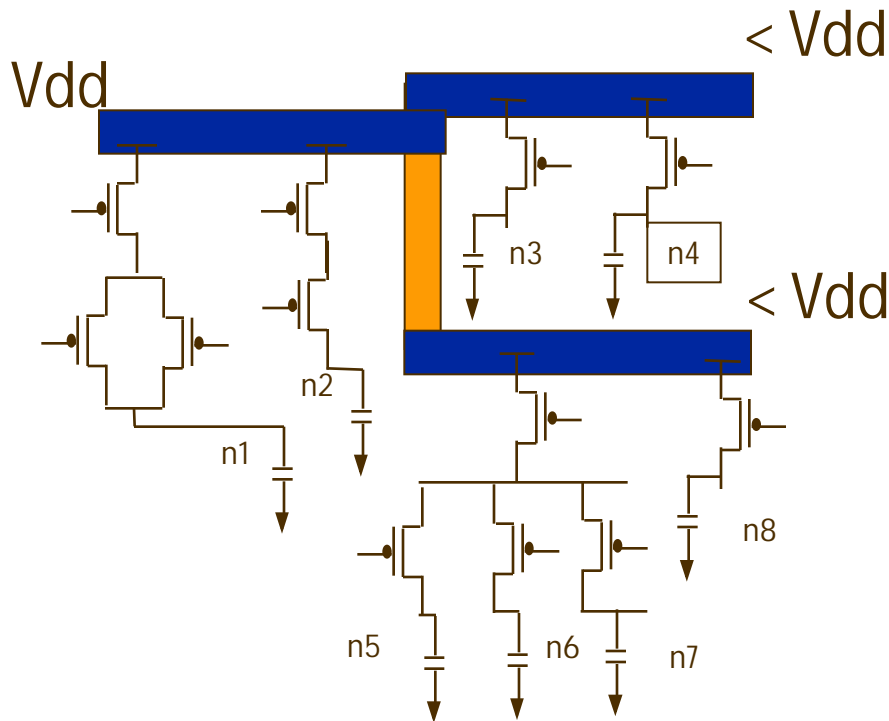


Global wires limit the system performance

Purpose of Power Distribution

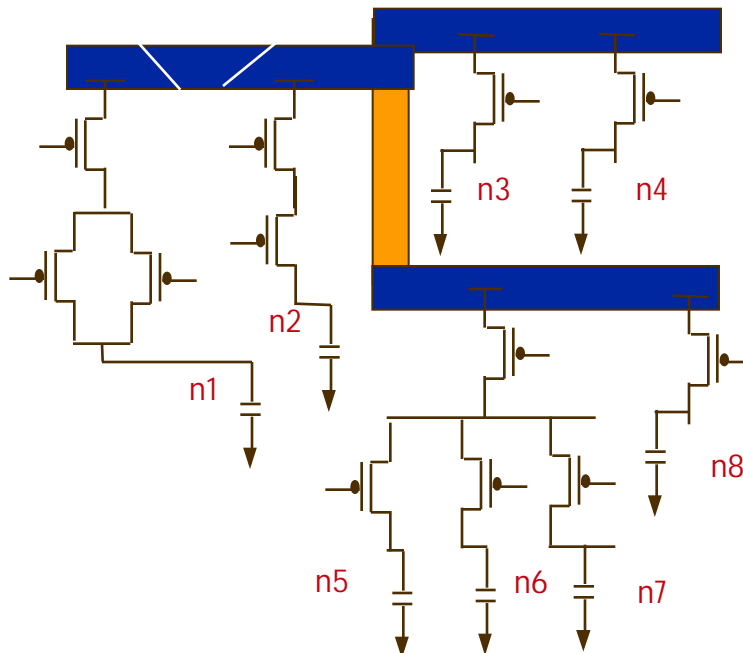
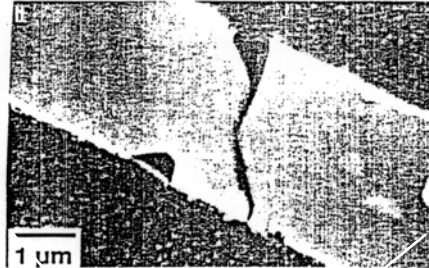
- Goal of power distribution system is to deliver the required current across the chip while maintaining the voltage levels necessary for proper operation of logic circuits
 - Must route both power and ground to all gates
 - Design Challenges:
 - How many power and ground pins should we allocate?
 - Which layers of metal should be used to route power/ground?
 - How wide should be make the wire to minimize voltage drops and reliability problems
 - How do we maintain V_{DD} and Gnd within noise budget?
 - How do we verify overall power distribution system?
-

Power Distribution Issues - IR Drop



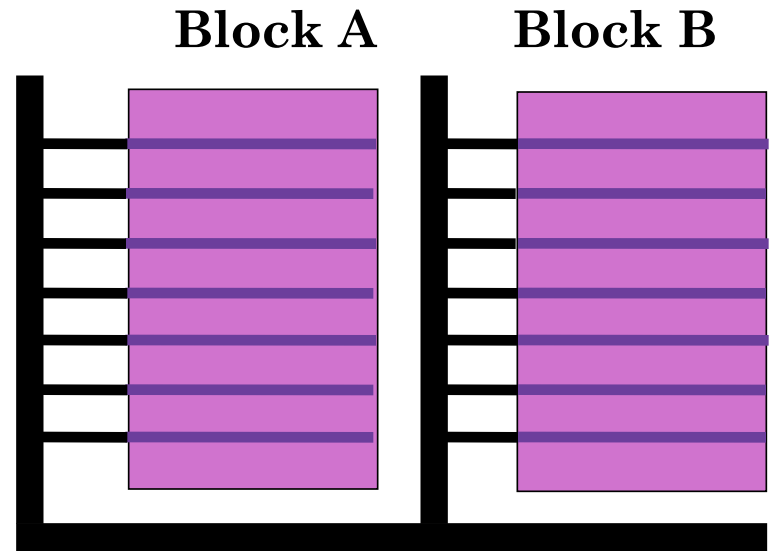
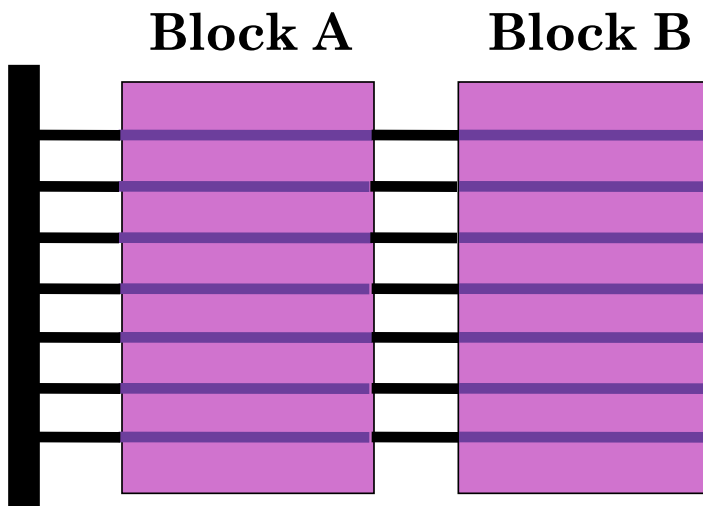
- Narrow line widths increase metal line resistance
- As current flows through power grid, voltage drops occur
- Actual voltage supplied to transistors is less than V_{dd}
- Impacts speed and functionality
- Need to choose wire widths to handle current demands of each segment

Power Grid Issues - Electromigration

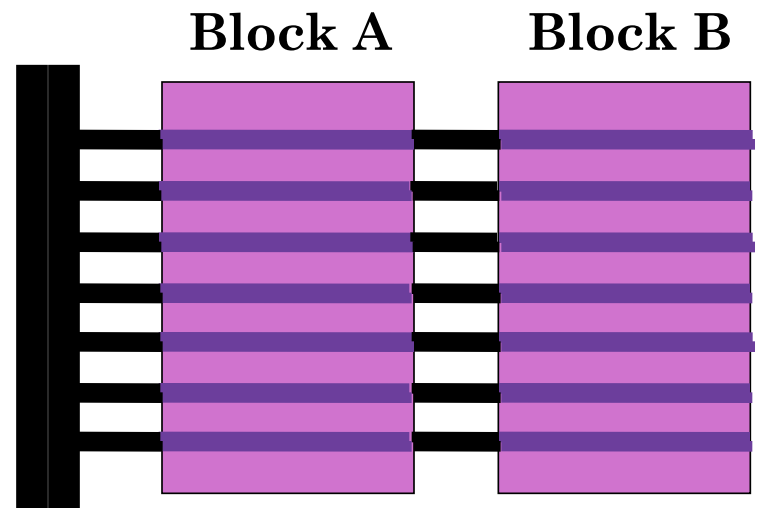
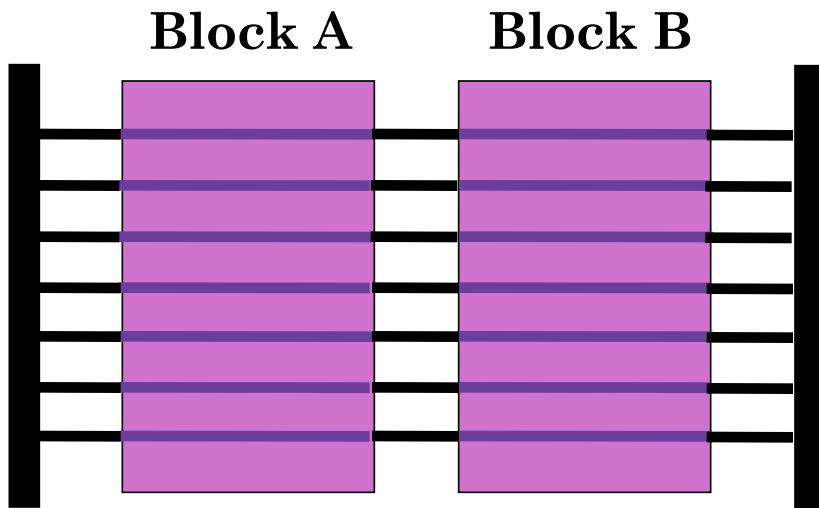


- As current flows down narrow wires, metal begins to migrate
- Metal lines break over time due to metal fatigue
- Based on average/peak current density
- Need to widen wires enough to avoid this phenomenon

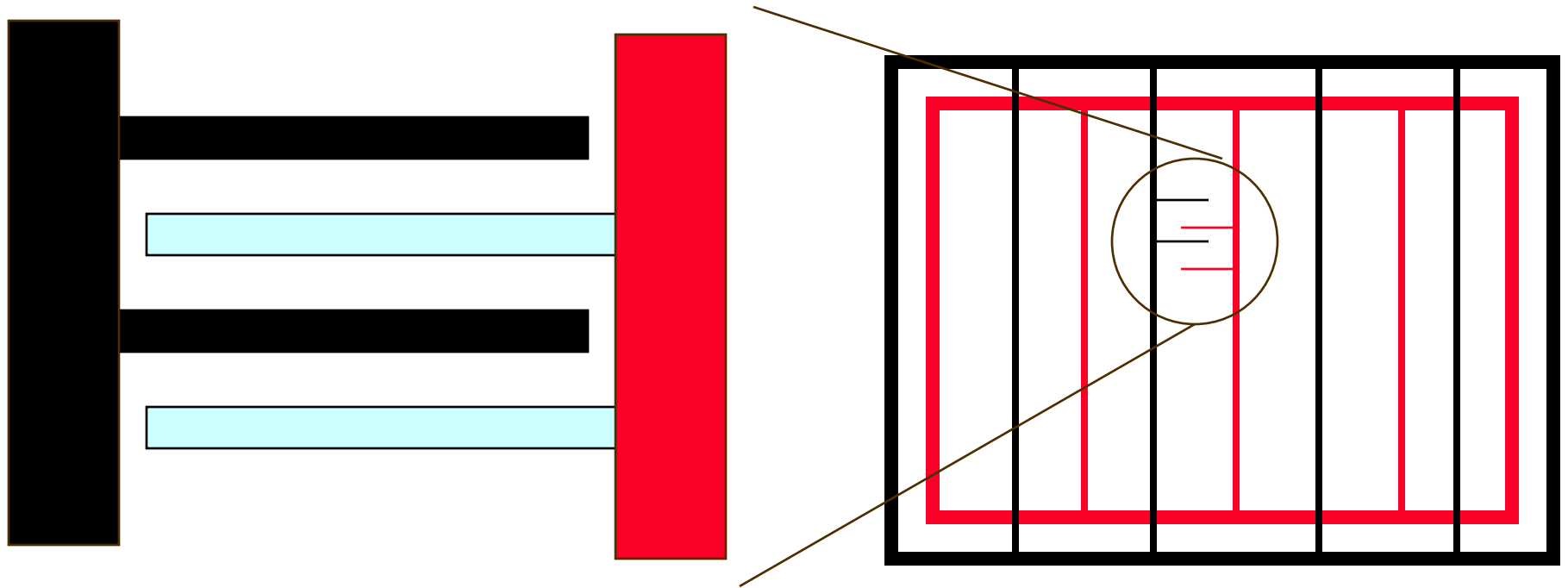
Power Routing Examples



Simple Routing Examples



Interleaved Power/Ground Routing



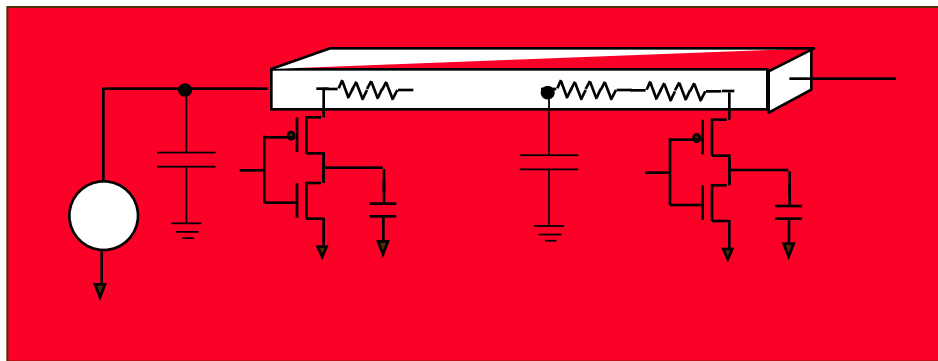
Interleaved Vdd/Vss

Ldi/dt Effects in the Power Supply

- In addition to IR drop, power system inductance is also an issue
- Inductance may be due to power pin, power bump or power grid
- Overall voltage drop is:

$$V_{\text{drop}} = IR + Ldi/dt$$

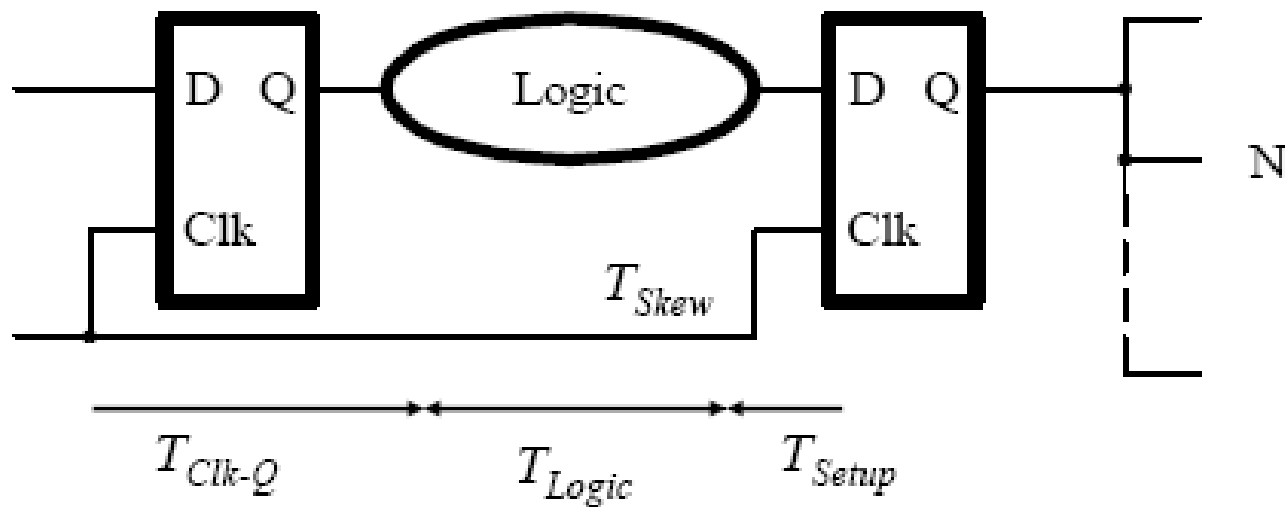
- Distribute decoupling capacitors (de caps) liberally throughout design
 - Capacitors store up charge
 - Can provide instantaneous source of current for switching



Clock Design Issues

- Clock cycle depends on a number of factors:

$$T_{cycle} = T_{Clk-Q} + T_{Logic} + T_{setup} + T_{skew}$$



Sources of clock skew

Main sources:

1. Imbalance between different paths from clock source to FF's
 - interconnect length determines RC delays
 - capacitive coupling effects cause delay variations
 - buffer sizing
 - number of loads driven
 2. Process variations across die
 - interconnect and devices have different statistical variations
-

Power Dissipation in Clocks

- Significant power dissipation can occur in clocks in high-performance designs:
 - clock switches on every cycle so $P = CV^2f$ (i.e., $\alpha=1$)
 - clock capacitance can be ~nF range, say 1nF = 1000pF
 - assuming a power supply of 1.8V, $CV = 1800\text{pC}$ of charge
 - if clock switches every 2ns (500MHz), that's 0.9A
 - for $V_{DD} = 1.8\text{V}$, $P = IV = 0.9(1.8) = 1.6\text{W}$ in the clock circuit alone
 - Much of the power (and the skew) occurs in the final drivers due to the sizing up of buffers to drive the flip-flops
 - Key to reducing the power is to examine equation CV^2f and reduce the terms wherever possible
 - V_{DD} is usually given to us; would not want to reduce swing due to coupling noise, etc.
 - Look more closely at C and f
-

Reducing Power in Clocking

- Gated Clocks:
 - can gate clock signals through AND gate before applying to flip-flop; this is more of a total chip power savings
 - all clock trees should have the same type of gating whether they are used or not, and at the same level - total balance

- Reduce overall capacitance (again, shielding vs. spacing)



(a) higher total cap./less area



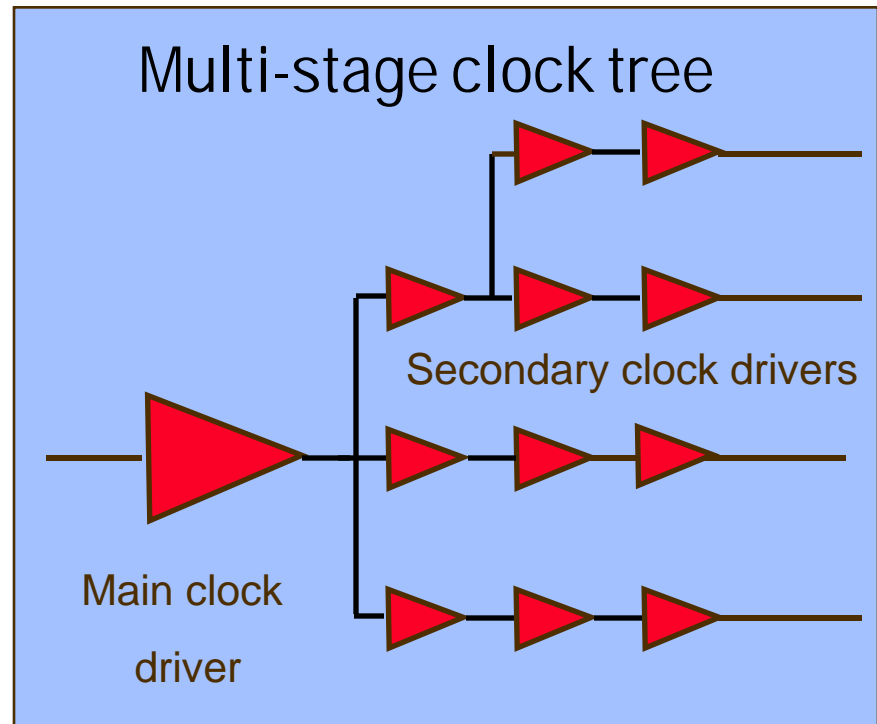
(b) lower cap./ more area

- Tradeoff between the two approaches due to coupling noise
 - approach (a) is better for inductive noise; (b) is better for capacitive noise
-

Clock Design

Tree

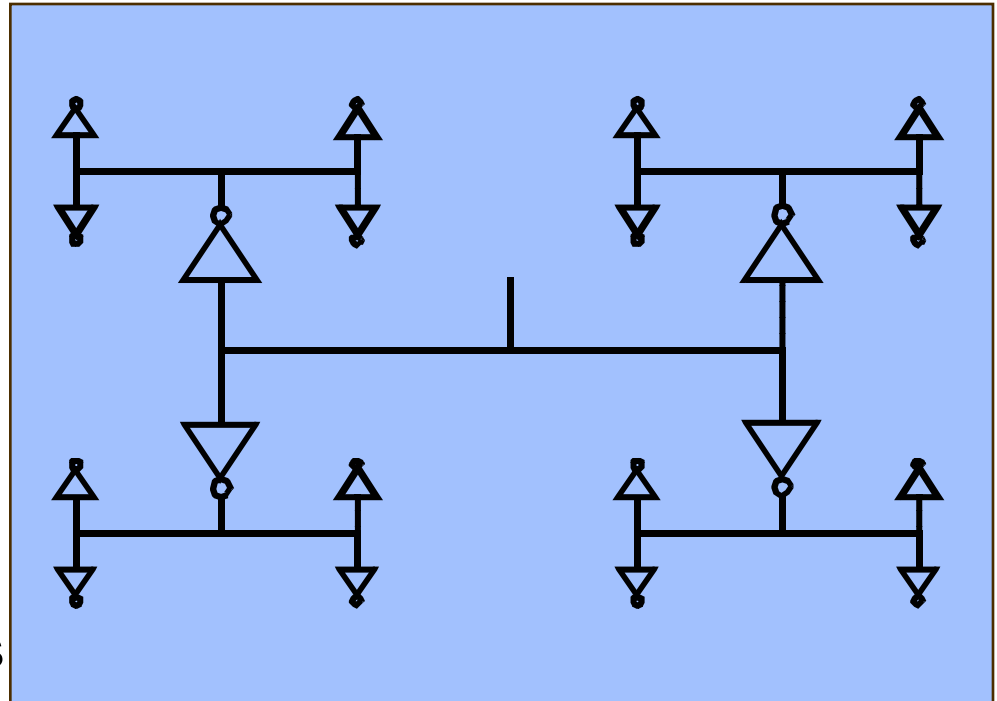
- Minimal area cost
- Requires clock-tree management
- Use a large super buffer to drive downstream buffers
- Balancing may be an issue



Clock Configurations

H-Tree

- Place clock root at center of chip and distribute as an H structure to all areas of the chip
- Clock is delayed by an equal amount to every section of the chip
- Local skew inside blocks is kept within tolerable limits



Clock Configurations

Grid

- Greater area cost
- Easier skew control
- Increased power consumption
- Electromigration risk increased at drivers
- Severely restricts floorplan and routing

